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The invention relates to optoelectronics, namely to a process for obtaining photosensitive material on base of amorphous chalcogenide semiconductor $As_2(S_xSe_{1-x})_3$ that can be used as optical and holographic image recording medium, optical sensors, in microlithography etc.

The process consists in that there are separately dissolved the As_2S_3 and As_2Se_3 in monoethanolamine or in ethylenediamine at the temperature of 20...40°C, then the mixtures are cooled up to the room temperature and are mixed in a ratio determined by the value x, afterwards the mixture is deposited on a support and is dried in the air at the temperature up to 40°C, during 2 hours.

Claims: 1

Fig.: 2